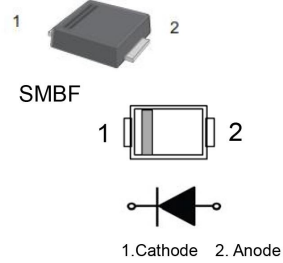




Features:

- ☐ Metal silicon junction, majority carrier conduction
- ☐ For surface mounted applications
- ☐ Low power loss, high efficiency
- ☐ Fast switching for high efficiency
- ☐ High forward surge current capability
- ☐ For use in low voltage, high frequency inverters



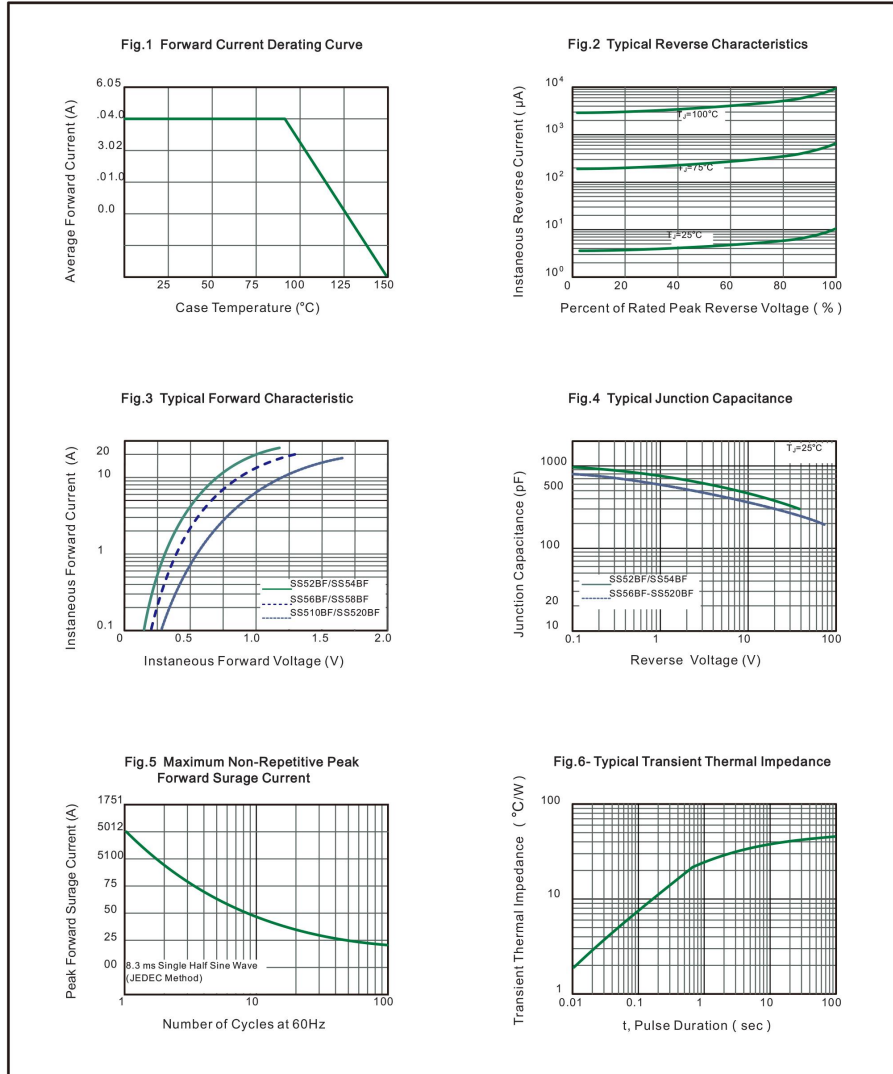
Absolute Maximum Ratings* (TA=25°C Unless otherwise noted)

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz resistive or inductive load, for capacitive load, derate by 20 %

Parameter	Symbols	CH52BF	CH54BF	CH56BF	CH58BF	CH510BF	CH512BF	CH515BF	CH520BF	Units
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	20	40	60	80	100	120	150	200	V
Maximum RMS voltage	V _{RMS}	14	28	42	56	70	84	105	140	V
Maximum DC Blocking Voltage	V _{DC}	20	40	60	80	100	120	150	200	V
Maximum Average Forward Rectified Current	I _{F(AV)}	5.0								A
Peak Forward Surge Current,8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	120								A
Max Instantaneous Forward Voltage at 5A	V _F	0.55	0.70	0.85				0.95		V
Maximum DC Reverse Current at Rated DC Reverse Voltage T _a = 25°C T _a =100°C	I _R	0.5 5			0.5 5			0.5 5		mA
Typical Junction Capacitance ⁽¹⁾	C _j	500	300							pF
Typical Thermal Resistance ⁽²⁾	R _{θJA}	45								°C/W
Operating Junction Temperature Range	T _j	-55 ~ +125				-55 ~ +150				°C
Storage Temperature Range	T _{stg}	-55 ~ +150								°C

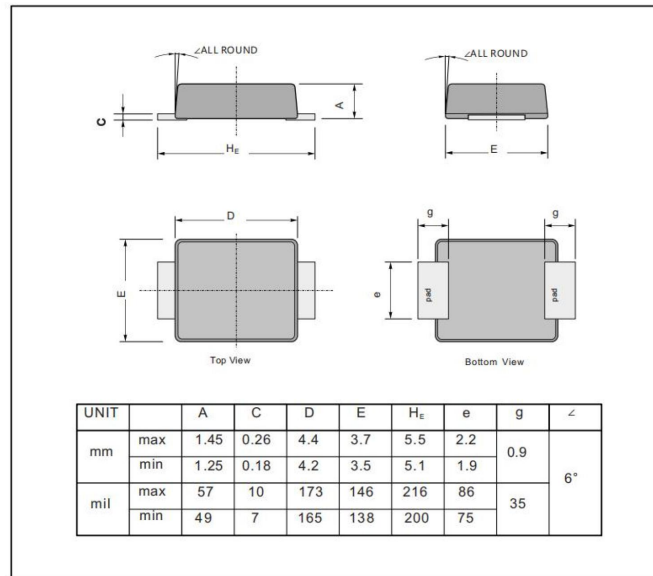
(1) Measured at 1 MHz and applied reverse voltage of 4 V.D.C

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.



Package Dimension

SMBF



The recommended mounting pad size

